SGC-2363Z

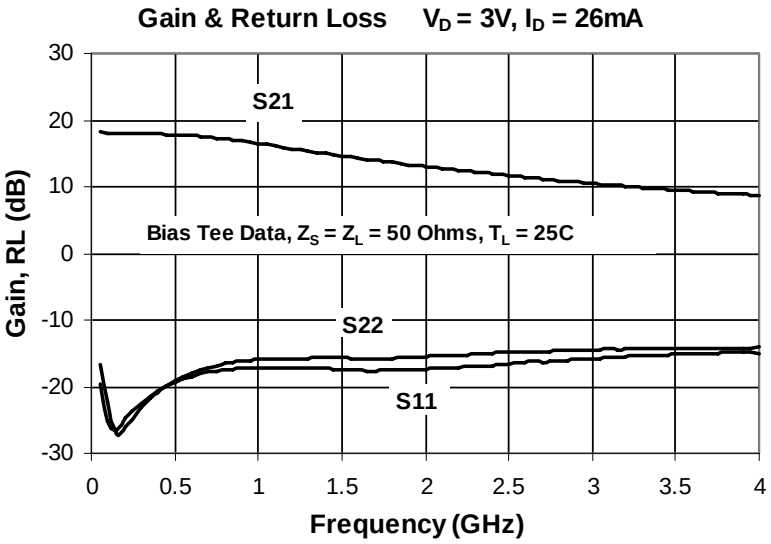
50-4000 MHz Active Bias Silicon Germanium Cascadable Gain Block



RoHS Compliant & Green Package

Product Description

Sirenza Microdevices' SGC-2363Z is a high performance SiGe HBT MMIC amplifier utilizing a Darlington configuration with a patented active-bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 3V supply, the SGC-2363Z does not require a dropping resistor as compared to typical Darlington amplifiers. The SGC-2363Z is designed for high linearity 3V gain block applications that require small size and minimal external components. It is internally matched to 50 ohms.



Product Features

- Single, Fixed 3V Supply
- No Dropping Resistor Required
- Patented Self-Bias Circuitry
- P1dB = 10.1 dBm at 1950 MHz
- OIP3 = 23 dBm at 1950 MHz
- Robust 1000V ESD, Class 1C HBM

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS, WCDMA
- IF Amplifier
- Wireless Data, Satellite

Symbol	Parameters	Units	Frequency	Min.	Typ.	Max.
G	Small Signal Gain	dB	850 MHz 1950 MHz 2400 MHz	15.5 11.6	17.0 13.1 12.3	18.5 14.6
P_{1dB}	Output Power at 1dB Compression	dBm	850 MHz 1950 MHz 2400 MHz	9.1	10.4 10.1 9.6	
OIP_3	Output Third Order Intercept Point	dBm	850 MHz 1950 MHz 2400 MHz	21	23.0 23.0 24.0	
IRL	Input Return Loss	dB	1950 MHz	12.0	15.0	
ORL	Output Return Loss	dB	1950 MHz	10.5	14.5	
NF	Noise Figure	dB	1930 MHz		3.7	4.8
V_D	Device Operating Voltage	V			3	
I_D	Device Operating Current	mA		22	26	30
Rth, j-l	Thermal Resistance (junction to lead)	°C/W			255	

Test Conditions: V_D = 3.0V I_D = 26mA T_L = 25°C OIP_3 Tone Spacing = 1MHz
Bias Tee Data Z_S = Z_L = 50 Ohms Pout per tone = -5 dBm

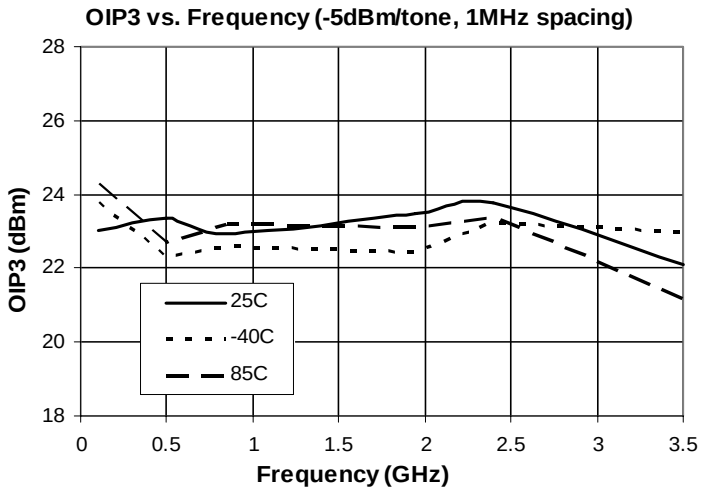
The information provided herein is believed to be reliable at press time. Sirenza Microdevices assumes no responsibility for inaccuracies or omissions. Sirenza Microdevices assumes no responsibility for the use of this information, and all such information shall be entirely at the user's own risk. Prices and specifications are subject to change without notice. No patent rights or licenses to any of the circuits described herein are implied or granted to any third party. Sirenza Microdevices does not authorize or warrant any Sirenza Microdevices product for use in life-support devices and/or systems. Copyright 2007 Sirenza Microdevices, Inc.. All worldwide rights reserved.

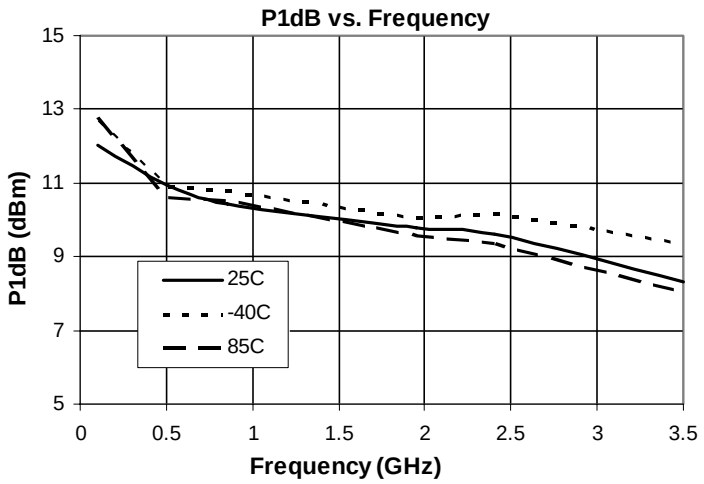
Typical RF Performance at Key Operating Frequencies (Bias Tee)

Symbol	Parameter	Unit	Frequency (MHz)					
			100	500	850	1950	2400	3500
G	Small Signal Gain	dB	18.4	18.1	17.0	13.1	12.3	9.8
OIP_3	Output Third Order Intercept Point	dBm	23.0	23.5	23.0	23.0	24.0	22.0
P_{1dB}	Output Power at 1dB Compression	dBm	12.1	11.0	10.4	10.1	9.6	8.3
IRL	Input Return Loss	dB	23.5	19.0	18.0	15.0	16.5	14.0
ORL	Output Return Loss	dB	22.5	18.5	16.5	14.5	13.0	12.5
S_{12}	Reverse Isolation	dB	20.5	21.5	22.0	20.5	20.0	19.0
NF	Noise Figure	dB	2.9	3.0	3.3	3.7	3.9	4.7

Test Conditions: V_D = 3V I_D = 26mA Typ. OIP_3 Tone Spacing = 1MHz, Pout per tone = -5 dBm
T_L = 25°C $Z_S = Z_L$ = 50 Ohms

Typical Performance with Bias Tee, V_D = 3V, I_D = 26mA





Absolute Maximum Ratings

Parameter	Absolute Limit
Max Device Current (I_{CE})	55 mA
Max Device Voltage (V_{CE})	4.5 V
Max. RF Input Power* (See Note)	+18 dBm
Max. Junction Temp. (T_J)	+150°C
Operating Temp. Range (T_L)	-40°C to +85°C
Max. Storage Temp.	+150°C

***Note:** Load condition, Z_L = 50 Ohms

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

$I_D V_D < (T_J - T_L) / R_{TH, j-l}$ $T_L = T_{LEAD}$

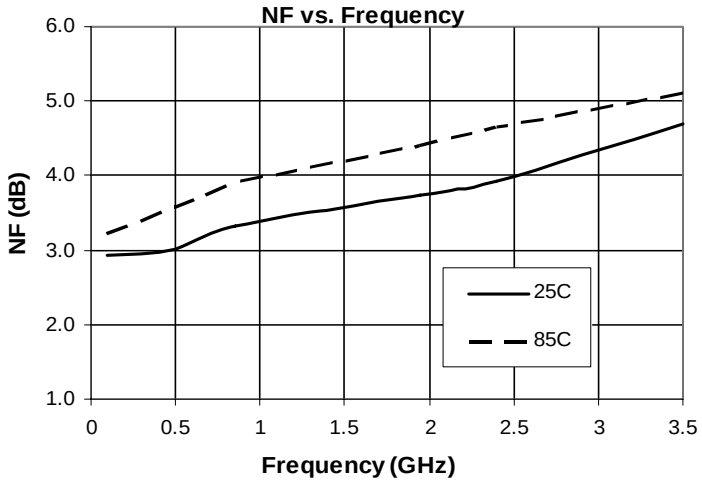
Reliability & Qualification Information

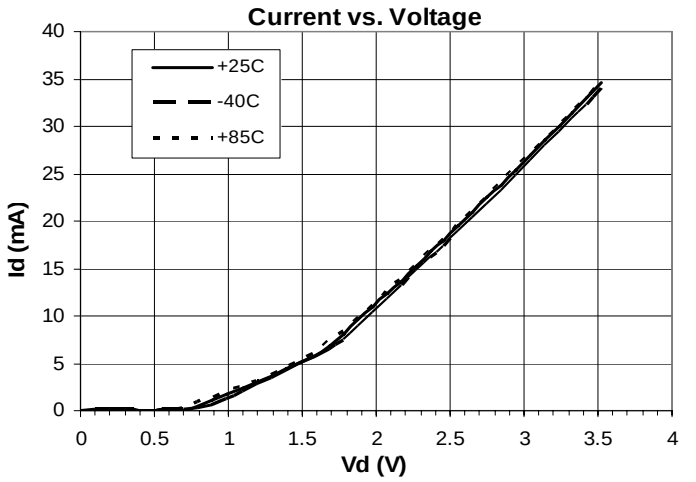
Parameter	Rating
ESD Rating - Human Body Model (HBM)	Class 1C
Moisture Sensitivity Level	MSL 1

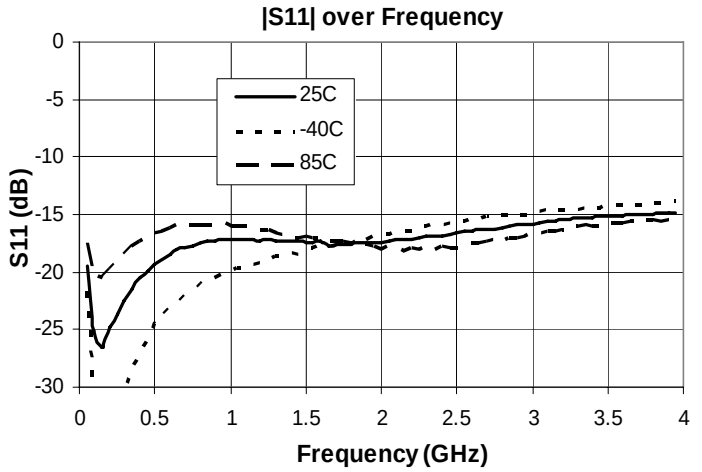
This product qualification report can be downloaded at *www.sirenza.com*

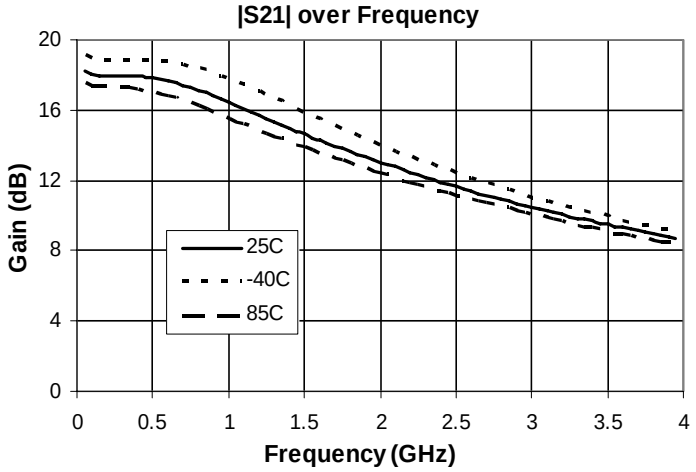
Caution: ESD sensitive
Appropriate precautions in handling, packaging and testing devices must be observed.

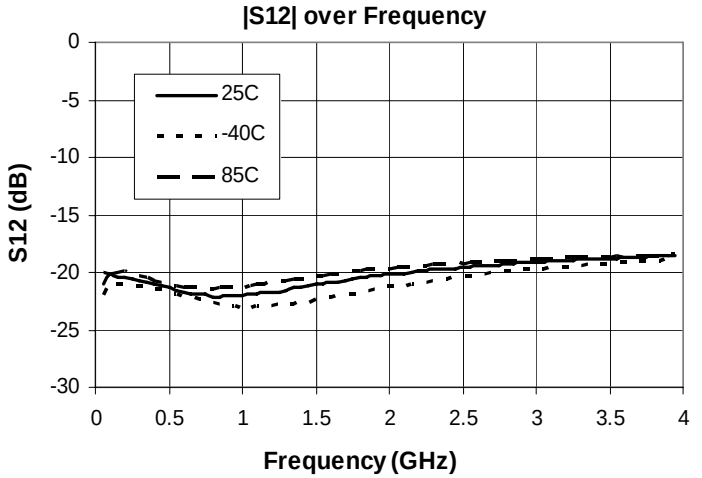
Typical Performance with Bias Tee, V_D= 3V, I_D= 26mA

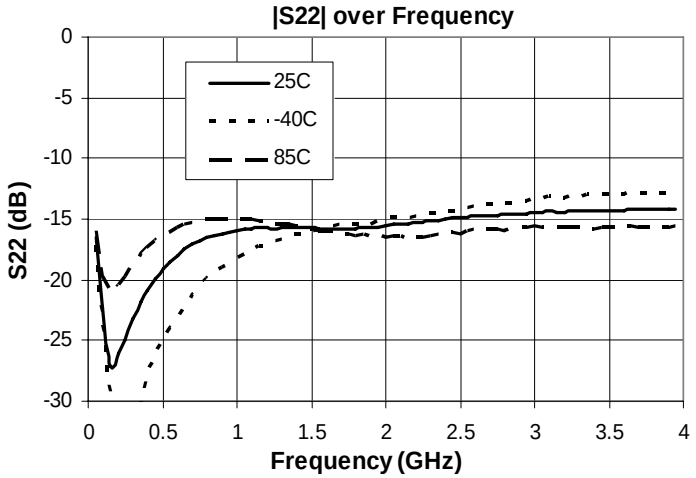




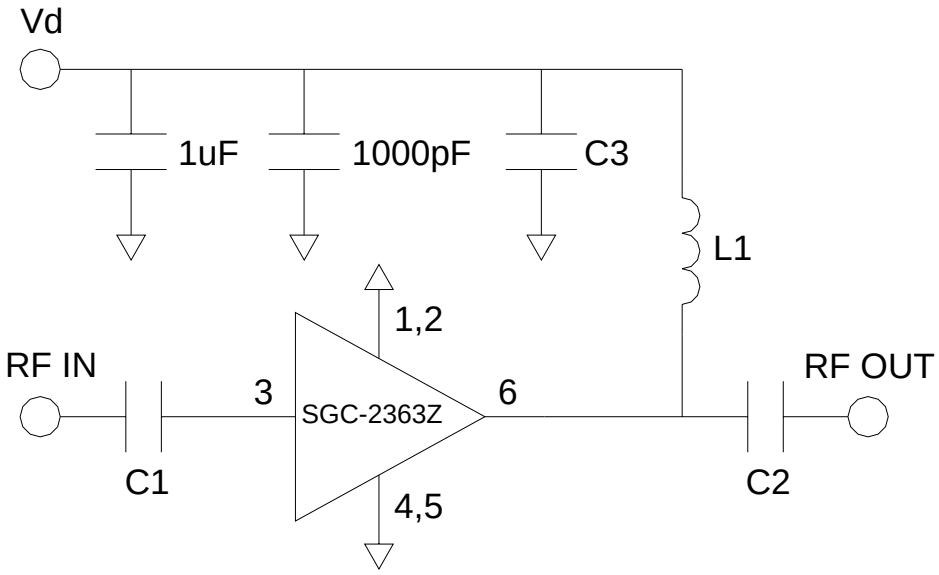




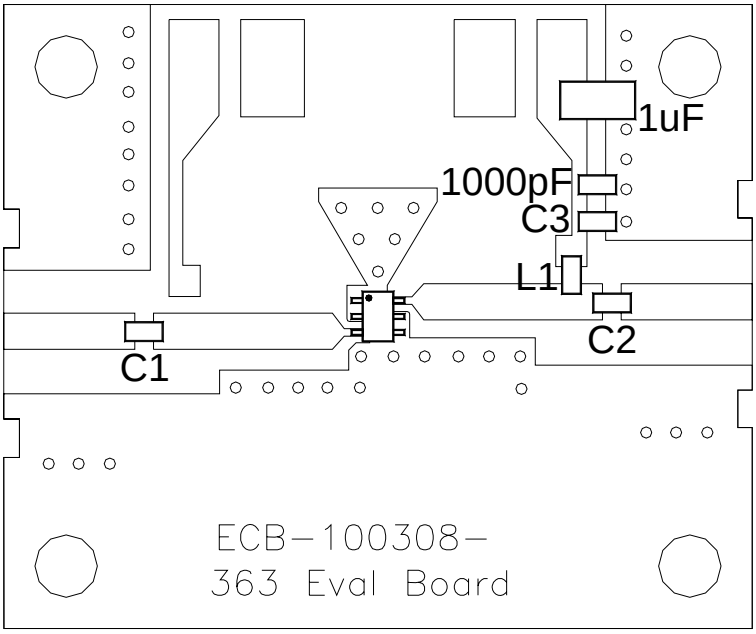




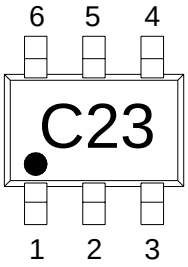
Basic Application Circuit



Application Circuit Element Values		
Reference Designator	100-2000MHz	2000-4000MHz
C1	1000pF	2.7pF
C2	100pF	6.8pF
C3	100pF	6.8pF
L1	150nH	39nH



Part Identification Marking & Pinout



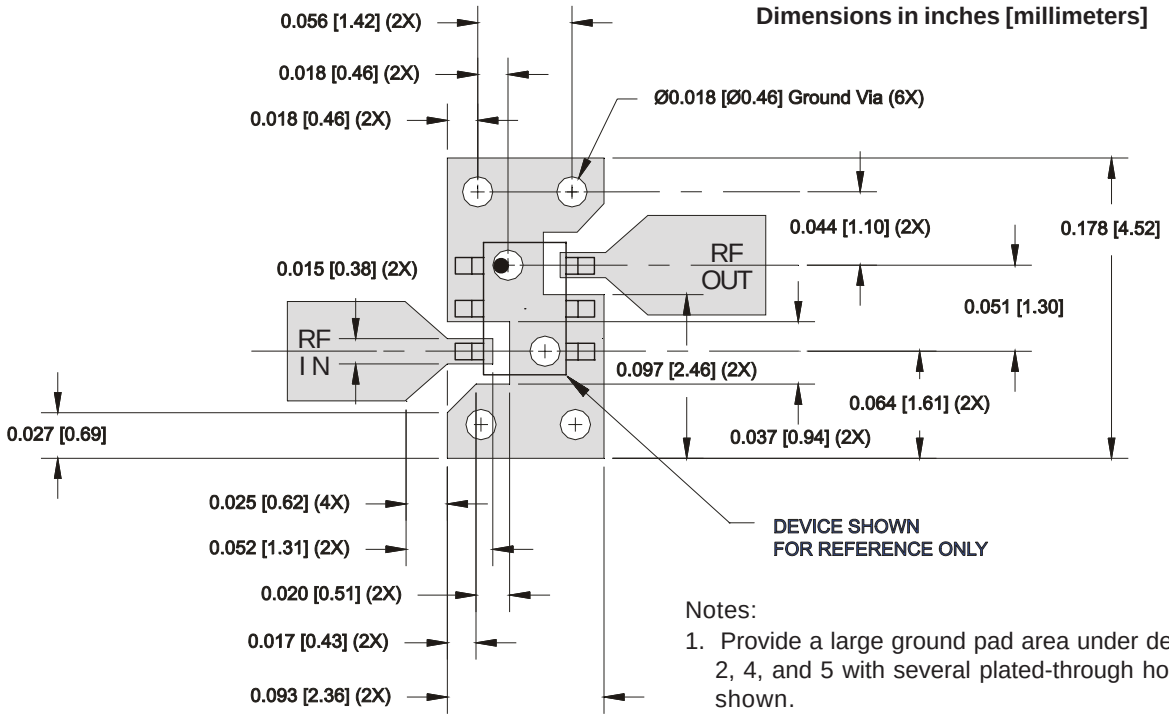
Pin #	Function	Description
3	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation
1,2,4,5	GND	Connection to ground. Use via holes as close to the device ground leads as possible to reduce ground inductance and achieve optimum RF performance
6	RF OUT / DC BIAS	RF output and bias pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.

Part / Evaluation Board Ordering Information

Part Number	Description	Reel Size	Devices / Reel
SGC-2363Z	Lead Free, RoHs Compliant	7"	3000
SGC-2363Z-EVB1	100-2000 MHz Evaluation Board	N/A	N/A
SGC-2363Z-EVB2	2000-4000 MHz Evaluation Board	N/A	N/A

SOT-363 PCB Pad Layout

Dimensions in inches [millimeters]



Notes:

1. Provide a large ground pad area under device pins 1, 2, 4, and 5 with several plated-through holes placed as shown.
2. 1-2 ounce finished copper thickness is recommended.
3. RF I/O lines are 50Ω

SOT-363 Nominal Package Dimensions

Dimensions in inches [millimeters]

A link to the SOT-363 package outline drawing with full dimensions and tolerances may be found on the product web page at www.sirenza.com.

